

Low-Band Carrier Aggregation Solution

(Preliminary Datasheet-Ver. 1.5)

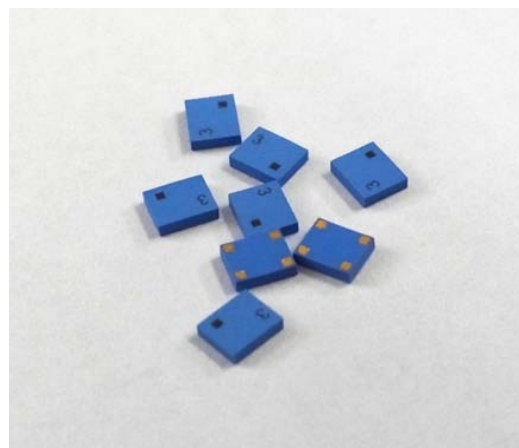


Applications

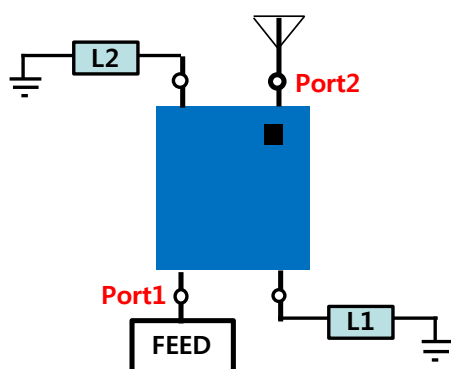
- ▶ Mobile device antennas for low frequency Inter-band carrier aggregation(B5&B12/B5&B17/B8&B20/B18&B28)

Features

- ▶ Wideband matching for antennas (Bandwidth enhancement up to 300%)
- ▶ No DC power supply and software control required
- ▶ Applicable to primary and secondary antennas
- ▶ Simplified circuit design than that of switchable antenna
- ▶ Capable of antenna sharing for variation handset models



Block Diagram

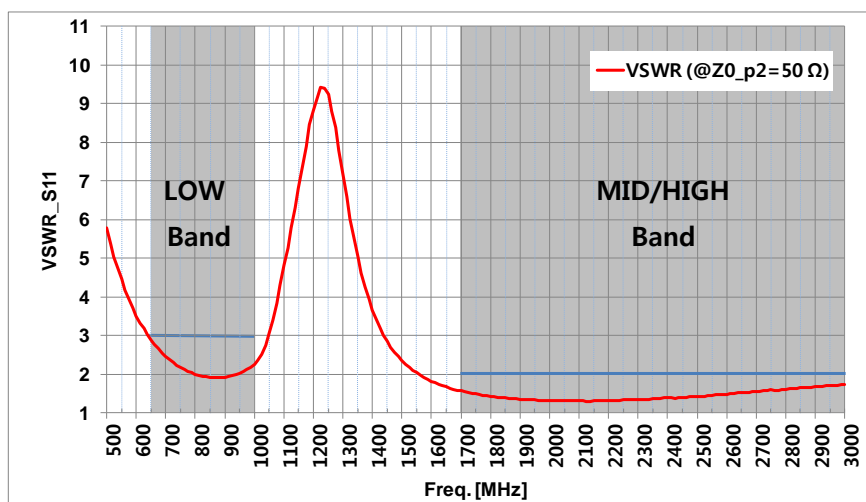


- ▶ Port 1 is connected to RF signal.
- ▶ Port 2 is connected to an antenna.
- ▶ L1 and L2 are external matching components.

Specifications

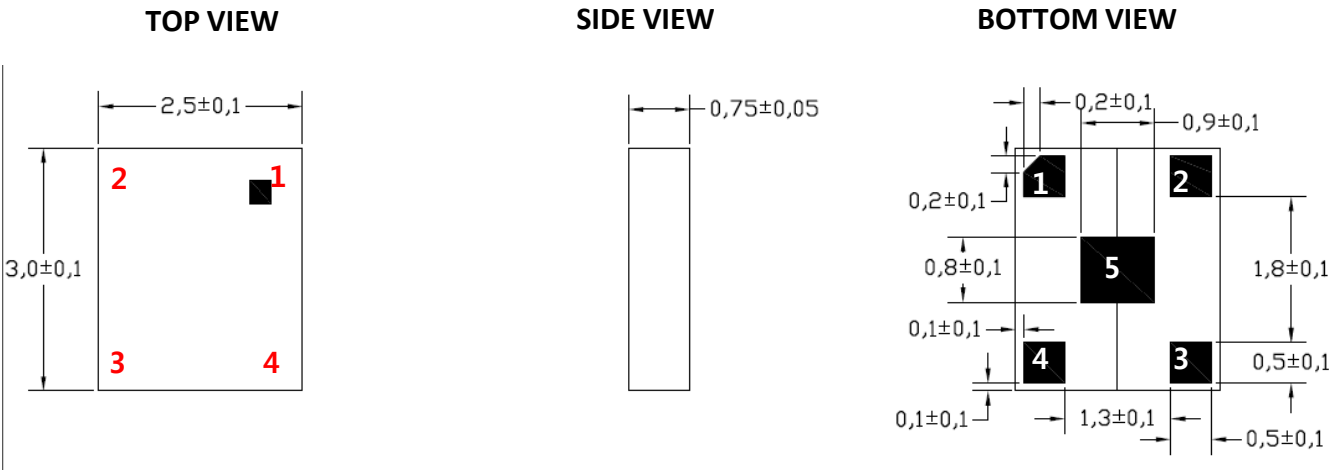
Dimensions [mm]	2.5 X 3.0 X 0.7
Applicable frequency range [MHz]	650~1000 (Low Band) / 1700~3000 (MID/HIGH Band)
*VSWR (:1) @port1	< 3 (Low Band) / < 2 (MID/HIGH Band)
Operating temperature [°C]	-40 to +85
Storage temperature [°C]	-40 to +125

* Specified VSWR values are measured in +25°C. Where, the port 2 is terminated with 50Ω and WBMC is connected L1(12nH) and L2(15nH).



Package outline

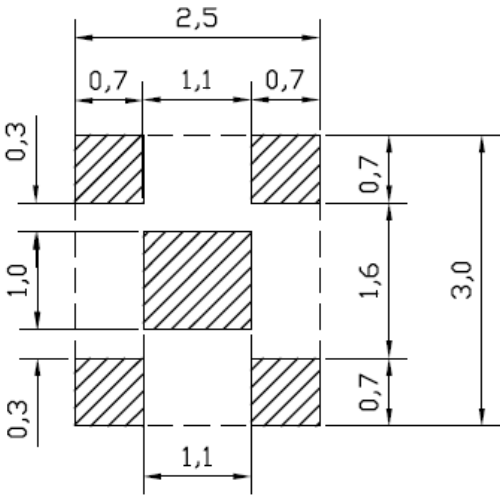
[Unit : mm]



Pin No.	Description
1	Port2 (Ant.)
2	L2 connected port
3	Port1 (Feed)
4	L1 connected port
5	Dummy pad

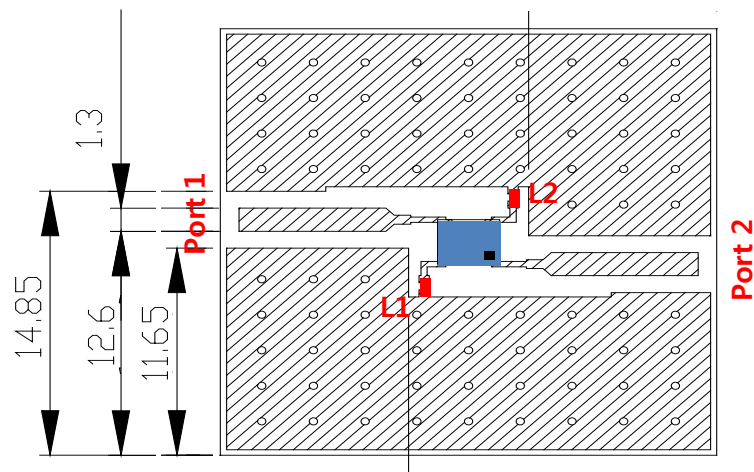
Land pattern

[Unit : mm]



Evaluation board I (2-Port)

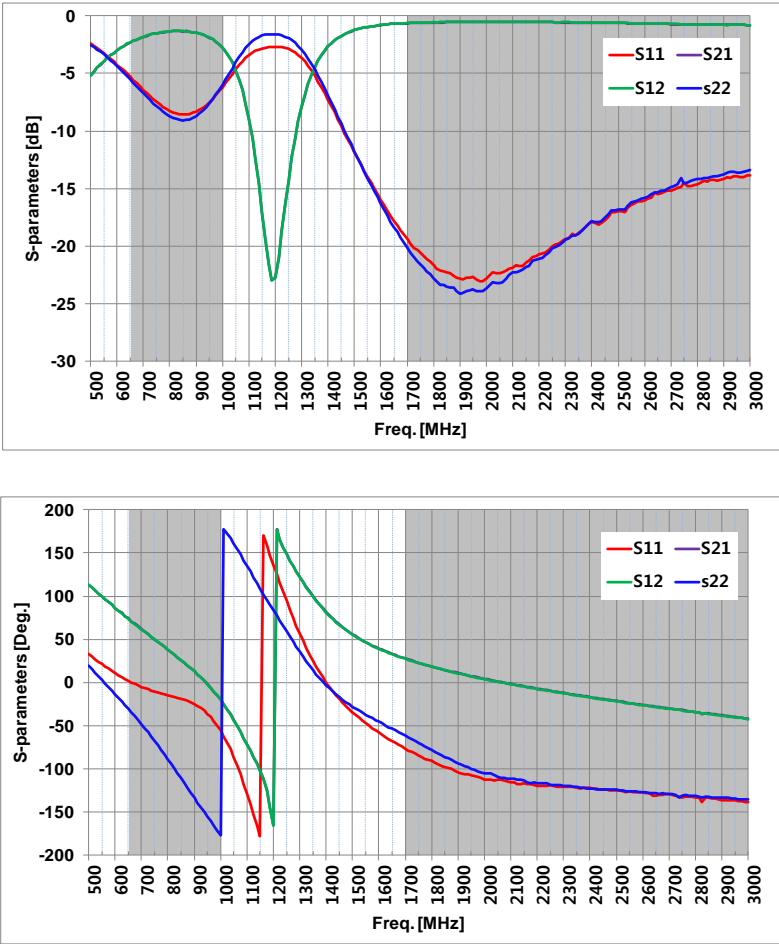
[Unit : mm]



Substrate
FR4 ($\epsilon_r=4.4$)
Thickness=0.8mm
Metal thickness=25um
Outline size = 24 X 24 mm

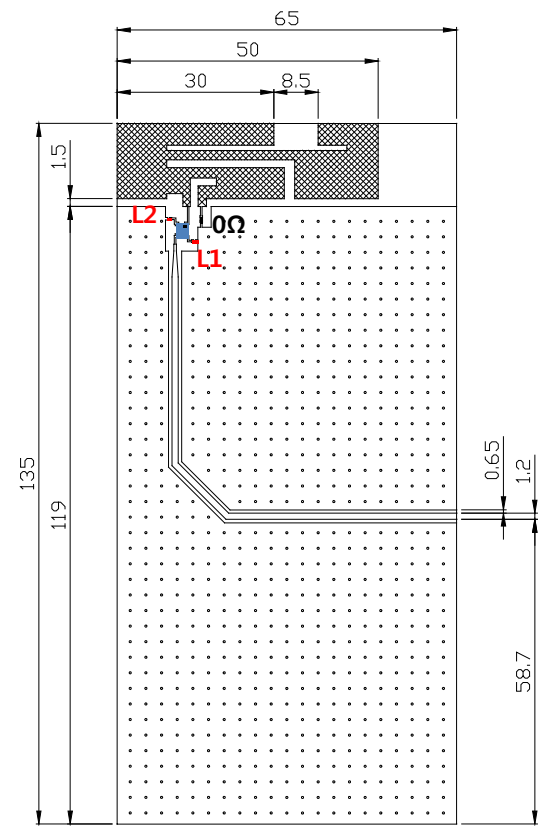
Parts list		
No.	Type	Value
L1	1005	10nH
L2		10nH

Typical data on EVB I



Evaluation board II (with ANT)

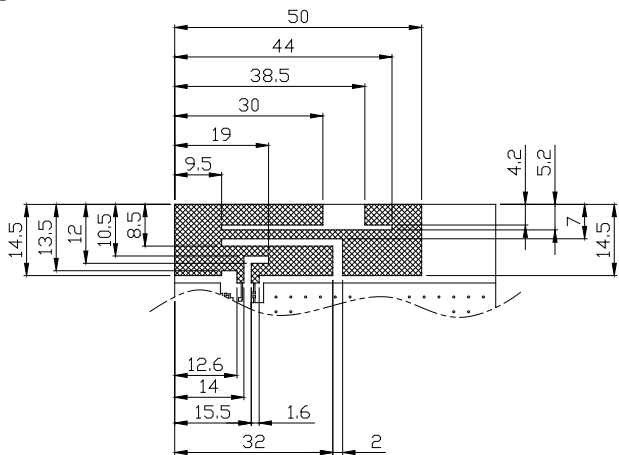
[Unit : mm]



Antenna

Type : Inverted-F

Non-ground size = 65 X 17 mm



Substrate

FR4 ($\epsilon_r=4.4$)

Thickness=0.8mm

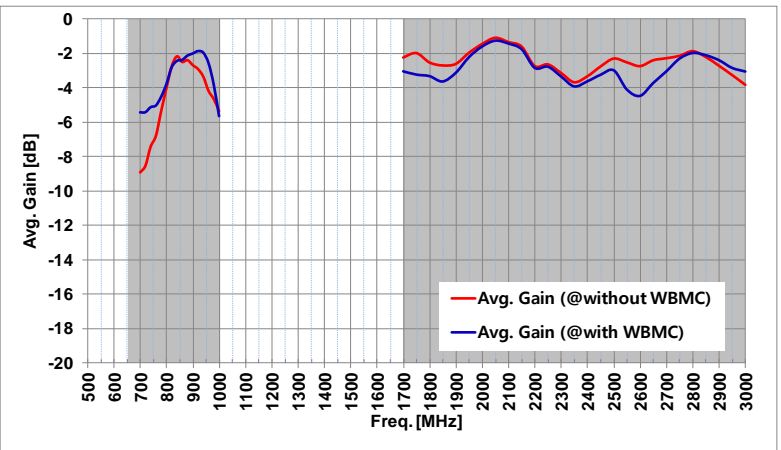
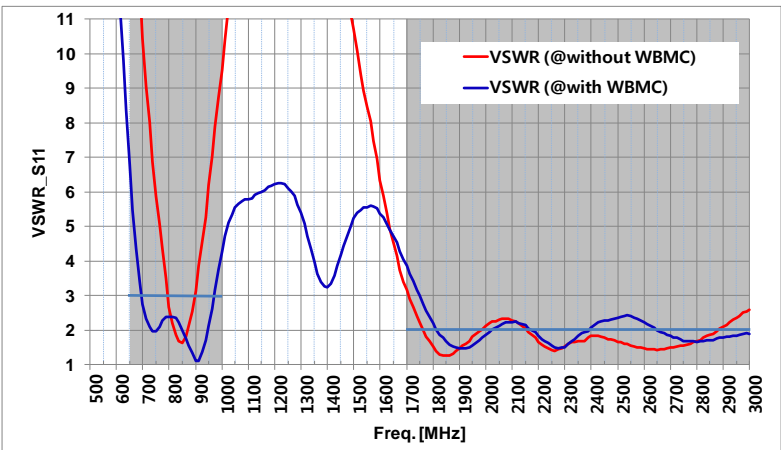
Metal thickness=25um

Outline size = 65 X 135 mm

Parts list

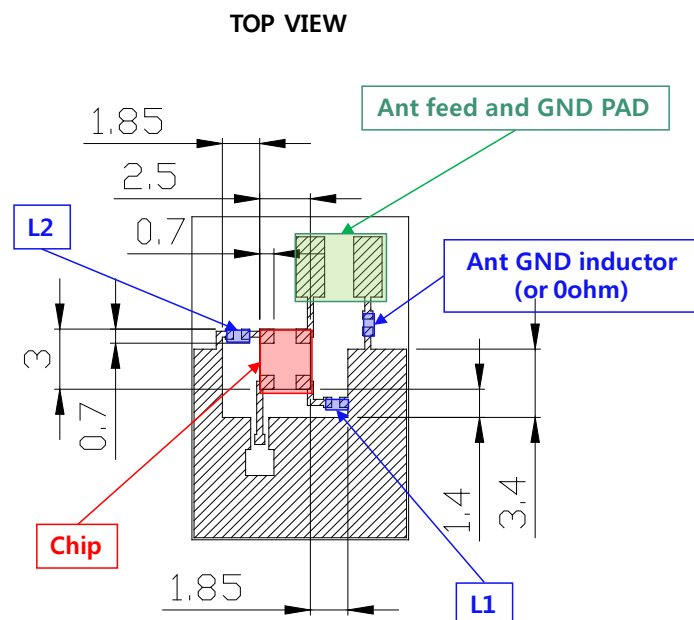
No.	Type	Value
L1	1005	10nH
L2		10nH

Typical data on EVBII



Application note

[Unit : mm]



- ▶ Metal ground under the area of chip, L1 and L2 must be removed.
- ▶ As the value of the antenna GND inductor increases, the radius of the impedance locus increases and the resonant frequency at Band I shifts toward the higher frequency side.
- ▶ As the value of L1 decreases, the resonant frequency near 900 MHz shifts toward the higher frequency side.
- ▶ As L2 decreases, the resonant frequency near 700 MHz increases.
- ▶ Available values of L1 and L2 are 4.7 nH up to 15 nH .

Part No (EMW)

Part No (EMW) EWM-3025-F0630EA0

E WM - 3025 - F0630 E A 0
 (1) (2) (3) (4) (5) (6) (7)

- (1) EMW
- (2) series : Wideband impedance Matching component
- (3) Dimensions First two disits : length(mm)
 Last two disits : Width(mm)
- (4) Matching band frequency F : Fequency
 First two disita : 0.6GHz
 Last two disits : 3 GHz
- (5) Packaging P : Embossed paper tape
 E : Embossed plastc tape
- (6) termination N : nickel barrier
 A : Au plating
- (7) Version Number